

# Bruce W Wessels

## List of Publications by Citations

**Source:** <https://exaly.com/author-pdf/6681906/bruce-w-wessels-publications-by-citations.pdf>

**Version:** 2024-04-23

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

249  
papers

7,301  
citations

41  
h-index

76  
g-index

253  
ext. papers

8,108  
ext. citations

4.6  
avg, IF

5.84  
L-index

#	Paper	IF	Citations
249	Crystal Growth of the Perovskite Semiconductor CsPbBr <sub>3</sub> : A New Material for High-Energy Radiation Detection. <i>Crystal Growth and Design</i> , <b>2013</b> , 13, 2722-2727	3.5	927
248	Strong Electron-Phonon Coupling and Self-Trapped Excitons in the Defect Halide Perovskites A <sub>3</sub> M <sub>2</sub> I <sub>9</sub> (A = Cs, Rb; M = Bi, Sb). <i>Chemistry of Materials</i> , <b>2017</b> , 29, 4129-4145	9.6	344
247	Luminescence of heteroepitaxial zinc oxide. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 138-140	3.4	274
246	High spectral resolution of gamma-rays at room temperature by perovskite CsPbBr single crystals. <i>Nature Communications</i> , <b>2018</b> , 9, 1609	17.4	246
245	Behavior of 2.8- and 3.2-eV photoluminescence bands in Mg-doped GaN at different temperatures and excitation densities. <i>Physical Review B</i> , <b>1999</b> , 59, 13176-13183	3.3	205
244	Excitonic emissions and above-band-gap luminescence in the single-crystal perovskite semiconductors CsPbBr <sub>3</sub> and CsPbCl <sub>3</sub> . <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	194
243	Dimensional reduction: a design tool for new radiation detection materials. <i>Advanced Materials</i> , <b>2011</b> , 23, 4163-7	24	147
242	Optical properties of the deep Mn acceptor in GaN:Mn. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 1731-1733	3.4	134
241	Epitaxial growth of BaTiO <sub>3</sub> thin films by organometallic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 41-43	3.4	134
240	Ferroelectric Epitaxial Thin Films for Integrated Optics. <i>Annual Review of Materials Research</i> , <b>2007</b> , 37, 659-679	12.8	125
239	Combinatorial Generation and Analysis of Nanometer- and Micrometer-Scale Silicon Features via Dip-Pen Nanolithography and Wet Chemical Etching. <i>Advanced Materials</i> , <b>2000</b> , 12, 1600-1603	24	113
238	Dielectric properties of epitaxial BaTiO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 2248-2250	3.4	112
237	Thin-film channel waveguide electro-optic modulator in epitaxial BaTiO <sub>3</sub> . <i>Applied Physics Letters</i> , <b>1997</b> , 71, 1783-1785	3.4	106
236	Investigation of the formation of the 2.8 eV luminescence band in p-type GaN:Mg. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 3011-3013	3.4	99
235	Thallium chalcogenides for X-ray and $\gamma$ -ray detection. <i>Journal of the American Chemical Society</i> , <b>2011</b> , 133, 10030-3	16.4	98
234	Photoluminescence band near 2.9 eV in undoped GaN epitaxial layers. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 3351-3354	2.5	93
233	Thallium Chalcogenide-Based Wide-Band-Gap Semiconductors: TlGaSe <sub>2</sub> for Radiation Detectors. <i>Chemistry of Materials</i> , <b>2011</b> , 23, 3120-3128	9.6	79

232	CsPbBr <sub>3</sub> perovskite detectors with 1.4% energy resolution for high-energy $\gamma$ -rays. <i>Nature Photonics</i> , <b>2021</b> , 15, 36-42	33.9	79
231	Electrical properties of p-type GaN:Mg codoped with oxygen. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 222-224	3.4	78
230	From 0D Cs <sub>3</sub> Bi <sub>2</sub> I <sub>9</sub> to 2D Cs <sub>3</sub> Bi <sub>2</sub> I <sub>6</sub> Cl <sub>3</sub> : Dimensional Expansion Induces a Direct Band Gap but Enhances Electron-Phonon Coupling. <i>Chemistry of Materials</i> , <b>2019</b> , 31, 2644-2650	9.6	72
229	Electrooptic modulation up to 40 GHz in a barium titanate thin film waveguide modulator. <i>Optics Express</i> , <b>2004</b> , 12, 5962-7	3.3	69
228	Thin film channel waveguides fabricated in metalorganic chemical vapor deposition grown BaTiO <sub>3</sub> on MgO. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 2968-2970	3.4	68
227	Resolving the Energy of $\gamma$ -Ray Photons with MAPbI <sub>3</sub> Single Crystals. <i>ACS Photonics</i> , <b>2018</b> , 5, 4132-4138	6.3	67
226	Cs <sub>2</sub> MIIMIV <sub>3</sub> Q <sub>8</sub> (Q = S, Se, Te): An Extensive Family of Layered Semiconductors with Diverse Band Gaps. <i>Chemistry of Materials</i> , <b>2013</b> , 25, 3344-3356	9.6	64
225	$\gamma$ -Particle Detection and Charge Transport Characteristics in the A <sub>3</sub> M <sub>2</sub> I <sub>9</sub> Defect Perovskites (A = Cs, Rb; M = Bi, Sb). <i>ACS Photonics</i> , <b>2018</b> , 5, 3748-3762	6.3	61
224	Thermal quenching of Er <sup>3+</sup> -related luminescence in In <sub>1-x</sub> GaxP. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 2657-2659	3.4	60
223	InAs/InP strained single quantum wells grown by atmospheric pressure organometallic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 1998-2000	3.4	60
222	Metal-Organic Chemical Vapor Deposition of Ferroelectric Oxide Thin Films for Electronic and Optical Applications. <i>Annual Review of Materials Research</i> , <b>1995</b> , 25, 525-546		59
221	Organometallic chemical vapor deposition of strontium titanate. <i>Journal of Applied Physics</i> , <b>1990</b> , 67, 3858-3861	2.5	58
220	Carbon-hydrogen complexes in vapor phase epitaxial GaN. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 357-359	3.4	56
219	Low-voltage, polarization-insensitive, electro-optic modulator based on a polydomain barium titanate thin film. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 4615-4617	3.4	55
218	Perovskite CsPbBr <sub>3</sub> single crystal detector for alpha-particle spectroscopy. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2019</b> , 922, 217-221	1.2	51
217	CsHgInS <sub>3</sub> : a New Quaternary Semiconductor for $\gamma$ -Ray Detection. <i>Chemistry of Materials</i> , <b>2012</b> , 24, 4434-4441	9.6	50
216	Electrical transport properties of epitaxial BaTiO <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 969-972	7.5	49
215	CsCdInQ <sub>3</sub> (Q = Se, Te): New Photoconductive Compounds As Potential Materials for Hard Radiation Detection. <i>Chemistry of Materials</i> , <b>2013</b> , 25, 2089-2099	9.6	46

214	Growth and characterization of OMVPE grown (In,Mn)As diluted magnetic semiconductor. <i>Journal of Electronic Materials</i> , <b>2001</b> , 30, 1408-1411	1.9	46
213	Local structure around Mn atoms in room-temperature ferromagnetic (In,Mn)As thin films probed by extended x-ray absorption fine structure. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 481-483	3-4	45
212	Photoluminescence properties of Er <sup>3+</sup> -doped BaTiO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 25-27	3-4	45
211	Magnetotransport properties of InMnSb magnetic semiconductor thin films. <i>Physical Review B</i> , <b>2010</b> , 82,	3-3	44
210	Nonlinear optical properties of textured strontium barium niobate thin films prepared by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1726-1728	3-4	44
209	Photoconductivity in the chalcogenide semiconductor, SbSeI: a new candidate for hard radiation detection. <i>Inorganic Chemistry</i> , <b>2013</b> , 52, 7045-50	5-1	43
208	Crystal Growth and Characterization of the X-ray and $\gamma$ -ray Detector Material Cs <sub>2</sub> Hg <sub>6</sub> S <sub>7</sub> . <i>Crystal Growth and Design</i> , <b>2012</b> , 12, 3250-3256	3-5	40
207	Photoconductivity in Tl <sub>6</sub> Si <sub>4</sub> : A Novel Semiconductor for Hard Radiation Detection. <i>Chemistry of Materials</i> , <b>2013</b> , 25, 2868-2877	9-6	39
206	Photoluminescent properties of Er-doped In <sub>1-x</sub> Ga <sub>x</sub> P prepared by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1991</b> , 59, 2317-2319	3-4	39
205	Defect Antiperovskite Compounds HgQI (Q = S, Se, and Te) for Room-Temperature Hard Radiation Detection. <i>Journal of the American Chemical Society</i> , <b>2017</b> , 139, 7939-7951	16.4	38
204	Interfacial structure and chemistry of epitaxial CoFe <sub>2</sub> O <sub>4</sub> thin films on SrTiO <sub>3</sub> and MgO substrates. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 181901	3-4	38
203	BaTiO <sub>3</sub> thin-film waveguide modulator with a low voltage-length product at near-infrared wavelengths of 0.98 and 1.55 microm. <i>Optics Letters</i> , <b>2005</b> , 30, 254-6	3	37
202	Microstructure of epitaxial potassium niobate thin films prepared by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 761-763	3-4	37
201	Epitaxial growth and strain relaxation of BaTiO <sub>3</sub> thin films on SrTiO <sub>3</sub> buffered (001) Si by molecular beam epitaxy. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2007</b> , 25, 1053		36
200	Magnetoamplification in a bipolar magnetic junction transistor. <i>Physical Review Letters</i> , <b>2010</b> , 105, 117202	9-24	35
199	Optical properties of InAs/InP strained single quantum wells grown by organometallic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , <b>1991</b> , 70, 405-408	2-5	35
198	Epitaxial potassium niobate thin films prepared by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 365-367	3-4	34
197	Relative dielectric constant of epitaxial BaTiO <sub>3</sub> thin films in the GHz frequency range. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 5274-5276	3-4	33

196	Ferromagnetic InMnSb multi-phase films study by aberration-corrected (scanning) transmission electron microscopy. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 07C311	2.5	32
195	Strain-driven spin reorientation in magnetite/barium titanate heterostructures. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 092510	3.4	32
194	Negative magnetoresistance in (In,Mn)As semiconductors. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	32
193	Preparation of high-Tc superconducting Bi-Sr-Ca-Cu-O films by organometallic chemical vapor deposition using second-generation fluorocarbon-based precursors. <i>Journal of Applied Physics</i> , <b>1991</b> , 69, 2743-2745	2.5	31
192	TlSn2I5, a Robust Halide Antiperovskite Semiconductor for X-Ray Detection at Room Temperature. <i>ACS Photonics</i> , <b>2017</b> , 4, 1805-1813	6.3	30
191	Crystal Growth of Tl4CdI6: A Wide Band Gap Semiconductor for Hard Radiation Detection. <i>Crystal Growth and Design</i> , <b>2014</b> , 14, 2401-2410	3.5	30
190	MOCVD of Epitaxial BaTiO3 Films Using a Liquid Barium Precursor. <i>Chemical Vapor Deposition</i> , <b>2000</b> , 6, 175-177		30
189	Monolayer abruptness in highly strained InAsxP1-x/InP quantum well interfaces. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 1142-1144	3.4	30
188	Blue emission band in compensated GaN:Mg codoped with Si. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	29
187	Ferromagnetism in (In,Mn)As diluted magnetic semiconductor thin films grown by metalorganic vapor phase epitaxy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2002</b> , 20, 1582		29
186	Luminescence quenching in Er-doped BaTiO3 thin films. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 1625-1627	3.4	29
185	Growth kinetics of ZnO prepared by organometallic chemical vapor deposition. <i>Journal of Materials Research</i> , <b>1988</b> , 3, 740-744	2.5	29
184	High-conductivity heteroepitaxial ZnSe films. <i>Applied Physics Letters</i> , <b>1980</b> , 37, 955-957	3.4	29
183	Deep level defects in heteroepitaxial zinc selenide. <i>Journal of Applied Physics</i> , <b>1982</b> , 53, 3076-3084	2.5	29
182	Morphological stability of strained-layer semiconductors. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1997</b> , 15, 1056		28
181	Ferromagnetic semiconductors and the role of disorder. <i>New Journal of Physics</i> , <b>2008</b> , 10, 055008	2.9	28
180	Optical properties of Mn4+ ions in GaN:Mn codoped with Mg acceptors. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 5320-5322	3.4	27
179	Epitaxial growth of SrTiO3 thin films by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 3298-3300	3.4	27

178	Cascaded spintronic logic with low-dimensional carbon. <i>Nature Communications</i> , <b>2017</b> , 8, 15635	17.4	27
177	High-field magnetoresistance in p-(In,Mn)As $\bar{\bar{b}}$ -InAs heterojunctions. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 072105	3.4	26
176	Optical investigation of electronic states of Mn <sup>4+</sup> ions in p-type GaN. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 042505	3.4	26
175	Hard Radiation Detection from the Selenophosphate Pb <sub>2</sub> P <sub>2</sub> Se <sub>6</sub> . <i>Advanced Functional Materials</i> , <b>2015</b> , 25, 4874-4881	15.6	25
174	Giant magnetoresistance of magnetic semiconductor heterojunctions. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	25
173	Epitaxial growth and strain relaxation of MgO thin films on Si grown by molecular beam epitaxy. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2006</b> , 24, 2586		25
172	Scanning tunneling optical spectroscopy of semiconductors. <i>Applied Physics Letters</i> , <b>1991</b> , 58, 1295-1296	3.4	24
171	Dynamic response of the dielectric and electro-optic properties of epitaxial ferroelectric thin films. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	23
170	Photonic Crystal Waveguide Electro-Optic Modulator With a Wide Bandwidth. <i>Journal of Lightwave Technology</i> , <b>2013</b> , 31, 1601-1607	4	22
169	High-temperature ferromagnetism in epitaxial (In,Mn)Sb films. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	22
168	Fast time-resolved x-ray diffraction in BaTiO <sub>3</sub> films subjected to a strong high-frequency electric field. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 3159-3161	3.4	22
167	Dynamic response of the electro-optic effect in epitaxial KNbO <sub>3</sub> . <i>Applied Physics Letters</i> , <b>1999</b> , 75, 2707-2709	3.4	22
166	Electroluminescence from Er-doped GaP. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 584-586	3.4	22
165	Direct thermal neutron detection by the 2D semiconductor LiInPSe. <i>Nature</i> , <b>2020</b> , 577, 346-349	50.4	21
164	Dielectric properties of epitaxial KNbO <sub>3</sub> ferroelectric thin films. <i>Journal of Materials Research</i> , <b>2002</b> , 17, 275-278	2.5	21
163	Thermal quenching properties of Er-doped GaP. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 1537-1539	3.4	21
162	Electronic and optical properties of Fe-doped InP prepared by organometallic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , <b>1986</b> , 60, 4342-4344	2.5	21
161	Spin-dependent magnetotransport in a p-InMnSb/n-InSb magnetic semiconductor heterojunction. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 193506	3.4	20

160	Diffuse Phase Transition in Epitaxial BaTiO <sub>3</sub> Thin Films. <i>Journal of Materials Research</i> , <b>2002</b> , 17, 669-674	2.5	20
159	Strained-layer InSb/GaSb quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 628-630	3.4	20
158	Characterization of Mn-doped InAs <sub>x</sub> P <sub>1-x</sub> grown by organometallic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 1155-1157	3.4	20
157	Thallos chalcogenide (Tl <sub>6</sub> I <sub>4</sub> Se) for radiation detection at X-ray and $\gamma$ energies. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2011</b> , 659, 333-335	1.2	19
156	Structure of organometallic chemical vapor deposited BaTiO <sub>3</sub> thin films on LaAlO <sub>3</sub> . <i>Journal of Electronic Materials</i> , <b>1993</b> , 22, 701-703	1.9	19
155	Perovskites with a Twist: Strong In <sup>1+</sup> Off-Centering in the Mixed-Valent CsInX <sub>3</sub> (X = Cl, Br). <i>Chemistry of Materials</i> , <b>2019</b> , 31, 9554-9566	9.6	18
154	A Spin-Diode Logic Family. <i>IEEE Nanotechnology Magazine</i> , <b>2012</b> , 11, 1026-1032	2.6	18
153	Polarization reversal and backswitching dynamics in epitaxial BaTiO <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 054113	2.5	18
152	On the microstructure, chemistry, and dielectric function of BaTiO <sub>3</sub> MOCVD thin films. <i>Journal of Materials Research</i> , <b>1994</b> , 9, 426-430	2.5	18
151	Detection of traps in high conductivity ZnSe by optical transient capacitance spectroscopy. <i>Journal of Applied Physics</i> , <b>1983</b> , 54, 4205-4208	2.5	18
150	Demonstration of Energy-Resolved $\gamma$ Ray Detection at Room Temperature by the CsPbCl Perovskite Semiconductor. <i>Journal of the American Chemical Society</i> , <b>2021</b> , 143, 2068-2077	16.4	18
149	Dynamic Disorder, Band Gap Widening, and Persistent Near-IR Photoluminescence up to At Least 523 K in ASnI <sub>3</sub> Perovskites (A = Cs <sup>+</sup> , CH <sub>3</sub> NH <sub>3</sub> <sup>+</sup> and NH <sub>2</sub> <sup>+</sup> ). <i>Journal of Physical Chemistry C</i> , <b>2018</b> , 122, 26353-26361	3.8	17
148	$\chi^{(2)}$ Modulator With 40-GHz Modulation Utilizing BaTiO <sub>3</sub> Photonic Crystal Waveguides. <i>IEEE Journal of Quantum Electronics</i> , <b>2017</b> , 53, 1-10	2	16
147	Local environment of ferromagnetically ordered Mn in epitaxial InMnAs. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 072505	3.4	16
146	Temperature dependent photoluminescent properties of InAs <sub>x</sub> P <sub>1-x</sub> /InP strained-layer quantum wells. <i>Journal of Applied Physics</i> , <b>1992</b> , 72, 3041-3045	2.5	16
145	Deep-level properties of Mn in InP. <i>Journal of Applied Physics</i> , <b>1990</b> , 67, 6882-6885	2.5	16
144	Heteroepitaxial growth of high mobility InAsP from the vapor phase. <i>Applied Physics Letters</i> , <b>1984</b> , 44, 766-768	3.4	16
143	Electron mobility and carrier concentration of heteroepitaxial zinc selenide. <i>Journal of Applied Physics</i> , <b>1982</b> , 53, 532-535	2.5	16

142	Magnetism and Mn Clustering in (In,Mn)Sb Magnetic Semiconductors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 24159-67	9.5	15
141	Hydrogen complexes in epitaxial BaTiO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 327-329	3.4	15
140	Highly efficient broadband second harmonic generation using polydomain epitaxial barium titanate thin film waveguides. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 221103	3.4	15
139	Low temperature deposition of epitaxial BaTiO <sub>3</sub> films in a rotating disk vertical MOCVD reactor. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2005</b> , 23, 1674		15
138	Epitaxial Niobate Thin Films and Their Nonlinear Optical Properties. <i>Materials Research Society Symposia Proceedings</i> , <b>1995</b> , 401, 211		15
137	Phase stability of epitaxial KTa <sub>1-x</sub> Nb <sub>x</sub> O <sub>3</sub> thin films deposited by metalorganic chemical vapor deposition. <i>Journal of Materials Research</i> , <b>2003</b> , 18, 106-110	2.5	15
136	Photoluminescence fatigue and inhomogeneous line broadening in semi-insulating Tl <sub>6</sub> SeI <sub>4</sub> single crystals. <i>Semiconductor Science and Technology</i> , <b>2016</b> , 31, 065009	1.8	14
135	Dependence of magnetic circular dichroism on doping and temperature in In <sub>1-x</sub> Mn <sub>x</sub> As epitaxial films. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	14
134	Yb-doped InP grown by metalorganic vapor phase epitaxy using a beta-diketonate precursor. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 566-568	3.4	14
133	Electron-beam-enhanced oxidation processes in II-VI compound semiconductors observed by high-resolution electron microscopy. <i>Journal of Applied Physics</i> , <b>1990</b> , 67, 1535-1541	2.5	14
132	Charge Transport and Observation of Persistent Photoconductivity in TlSeI Single Crystals. <i>Journal of Physical Chemistry Letters</i> , <b>2017</b> , 8, 1538-1544	6.4	13
131	An Unusual Crystal Growth Method of the Chalcogenide Semiconductor, Hg <sub>3</sub> S <sub>2</sub> Cl <sub>2</sub> : A New Candidate for Hard Radiation Detection. <i>Crystal Growth and Design</i> , <b>2016</b> , 16, 2678-2684	3.5	13
130	Three Dimensional Domain Structure in Epitaxial Barium Titanate Thin Films. <i>Journal of Electroceramics</i> , <b>2004</b> , 13, 89-93	1.5	13
129	Photoluminescent properties of Er-doped GaP deposited on Si. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 518-520	3.4	13
128	Defect structure of strontium titanate thin films. <i>Journal of Applied Physics</i> , <b>1993</b> , 74, 3927-3931	2.5	13
127	Scanning tunneling optical spectroscopy of semiconductor quantum well structures. <i>Applied Physics Letters</i> , <b>1991</b> , 58, 2538-2539	3.4	13
126	Nitrogen Doping of ZnO Prepared by Organometallic Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , <b>1989</b> , 152, 215		13
125	Comparative optical studies of p-type and unintentionally doped GaN: The influence of annealing. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 58-60	3.4	12



124	CuISe: A Metal-Inorganic Framework Wide-Bandgap Semiconductor for Photon Detection at Room Temperature. <i>Journal of the American Chemical Society</i> , <b>2018</b> , 140, 1894-1899	16.4	11
123	Cyclotron resonance in ferromagnetic InMnAs and InMnSb. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	11
122	Investigation of composition fluctuations in GaN:Mg using optical transmission spectroscopy, near-field scanning optical microscopy, and scanning Kelvin probe microscopy. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 023513	2.5	11
121	Nitrogen related defect centers in zinc selenide. <i>Journal of Applied Physics</i> , <b>1984</b> , 55, 1614-1616	2.5	11
120	Role of Stoichiometry in the Growth of Large Pb <sub>2</sub> P <sub>2</sub> Se <sub>6</sub> Crystals for Nuclear Radiation Detection. <i>ACS Photonics</i> , <b>2018</b> , 5, 566-573	6.3	11
119	Investigation of Semi-Insulating Cs <sub>2</sub> Hg <sub>6</sub> S <sub>7</sub> and Cs <sub>2</sub> Hg <sub>6</sub> -xCdx <sub>7</sub> Alloy for Hard Radiation Detection. <i>Crystal Growth and Design</i> , <b>2014</b> , 14, 5949-5956	3.5	10
118	Formation of native defects in the E <sub>γ</sub> detector material Cs <sub>2</sub> Hg <sub>6</sub> S <sub>7</sub> . <i>Applied Physics Letters</i> , <b>2012</b> , 101, 202103	3.4	10
117	Time-resolved differential transmission in MOVPE-grown ferromagnetic InMnAs. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	10
116	Investigation of defect levels in Cs <sub>2</sub> Hg <sub>6</sub> S <sub>7</sub> single crystals by photoconductivity and photoluminescence spectroscopies. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 063702	2.5	10
115	Photoconductive properties of the Er-doped InP. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 466-468	3.4	10
114	Carrier recombination mechanism in CsPbBr <sub>3</sub> revealed by time-resolved photoluminescence spectroscopy. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	10
113	Local electronic and magnetic structure of mixed ferrite multilayer materials. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	9
112	Using the infrared magnetorefractive effect to compare the magnetoresistance in (100) and (111) oriented Fe <sub>3</sub> O <sub>4</sub> films. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 09B102	2.5	9
111	Evidence of room temperature sp-d exchange in InMnAs epitaxial films. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 102505	3.4	9
110	Dielectric properties of plasma-spray-deposited BaTiO <sub>3</sub> and Ba <sub>0.68</sub> Sr <sub>0.32</sub> TiO <sub>3</sub> thick films. <i>Journal of Materials Research</i> , <b>2003</b> , 18, 1227-1231	2.5	9
109	Electronic and photoluminescent properties of InP prepared by flow modulation epitaxy. <i>Journal of Applied Physics</i> , <b>1992</b> , 71, 281-288	2.5	9
108	Electronic and optical properties of deep levels in iron-doped InAsP alloys. <i>Journal of Applied Physics</i> , <b>1988</b> , 64, 6770-6774	2.5	9
107	High conductivity zinc sulfoselenide thin films. <i>Applied Physics Letters</i> , <b>1982</b> , 41, 165-167	3.4	9

106	Refined Synthesis and Crystal Growth of Pb <sub>2</sub> P <sub>2</sub> Se <sub>6</sub> for Hard Radiation Detectors. <i>Crystal Growth and Design</i> , <b>2016</b> , 16, 5100-5109	3.5	9
105	TlSbS <sub>2</sub> : a Semiconductor for Hard Radiation Detection. <i>ACS Photonics</i> , <b>2017</b> , 4, 2891-2898	6.3	8
104	Dynamic response of polydomain ferroelectric barium titanate epitaxial thin films and its field dependence. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 064115	2.5	8
103	Thin Film Ferroelectrics for Guided Wave Devices. <i>Journal of Electroceramics</i> , <b>2004</b> , 13, 135-138	1.5	8
102	Observation of enhanced photoluminescence in erbium-doped semiconductor microdisk resonator. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 2843-2845	3.4	8
101	An Effective Purification Process for the Nuclear Radiation Detector Tl <sub>6</sub> SeI <sub>4</sub> . <i>Crystal Growth and Design</i> , <b>2018</b> , 18, 3484-3493	3.5	7
100	Transient photocurrent measurements in alkali chalcogenide ternary compound semiconductors. <i>Semiconductor Science and Technology</i> , <b>2013</b> , 28, 015022	1.8	7
99	High-field magnetic circular dichroism in ferromagnetic InMnSb and InMnAs: Spin-orbit-split hole bands and g factors. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	7
98	Emitter-Coupled Spin-Transistor Logic: Cascaded Spintronic Computing Beyond 10 GHz. <i>IEEE Journal on Emerging and Selected Topics in Circuits and Systems</i> , <b>2015</b> , 5, 17-27	5.2	7
97	Electronic structure of substitutional Mn in epitaxial In <sub>0.965</sub> Mn <sub>0.035</sub> Sb film. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 201905	3.4	7
96	Epitaxial Ferroelectric BaTiO <sub>3</sub> Thin Films for Microphotonic Applications. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 637, E1.9.1		7
95	Electroluminescence from forward-biased Er-doped GaP p-n junctions at room temperature. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 1126-1128	3.4	7
94	Inorganic Halide Perovskitoid TlPbI <sub>3</sub> for Ionizing Radiation Detection. <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 2006635	15.6	7
93	Improved Crystal Growth of Tl <sub>6</sub> SeI <sub>4</sub> for E-Ray Detection Material by Oxide Impurity Removal. <i>Crystal Growth and Design</i> , <b>2017</b> , 17, 6096-6104	3.5	6
92	Optical investigation of defects in semi-insulating Tl <sub>6</sub> I <sub>4</sub> S single crystals. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	6
91	Mercury and antimony chalcogenide semiconductors as new candidates for radiation detection applications at room temperature <b>2012</b> ,		6
90	Integration of MgO on Si(001) Using SrO and SrTiO <sub>3</sub> Buffer Layers by Molecular Beam Epitaxy. <i>Journal of Electroceramics</i> , <b>2004</b> , 13, 149-154	1.5	6
89	Metalorganic Molecular Beam Epitaxy of Magnesium Oxide on Silicon. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 619, 149		6

88	Electrical Properties of Oxygen Doped GaN Grown by Metalorganic Vapor Phase Epitaxy. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>2000</b> , 5, 301-307		6
87	BaTiO <sub>3</sub> thin films for optically active waveguides. <i>Integrated Ferroelectrics</i> , <b>1995</b> , 7, 25-31	0.8	6
86	The Effects of Domain Structure on the Electro-Optic Response of Potassium Niobate Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 453, 259		6
85	Rare-Earth Doped In <sub>1-x</sub> Ga <sub>x</sub> P Prepared by Metalorganic Vapor Phase Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , <b>1991</b> , 240, 195		6
84	Compensation in Ge-doped InP. <i>Journal of Applied Physics</i> , <b>1990</b> , 68, 606-609	2.5	6
83	Controlling the Vapor Transport Crystal Growth of Hg <sub>3</sub> Se <sub>2</sub> I <sub>2</sub> Hard Radiation Detector Using Organic Polymer. <i>Crystal Growth and Design</i> , <b>2019</b> , 19, 2074-2080	3.5	5
82	Emitter-coupled spin-transistor logic. <i>Journal of Parallel and Distributed Computing</i> , <b>2014</b> , 74, 2461-2469	4.4	5
81	Photo-induced current transient spectroscopy of single crystal Tl <sub>6</sub> I <sub>4</sub> Se. <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 115002	1.8	5
80	Photoluminescent properties of semiconducting Tl <sub>6</sub> I <sub>4</sub> Se. <i>Semiconductor Science and Technology</i> , <b>2012</b> , 27, 015016	1.8	5
79	Structural and magnetic properties of epitaxial In <sub>1-x</sub> Mn <sub>x</sub> Sb semiconductor alloys with x > 0.08. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 032801	1.3	5
78	Phase stability of heteroepitaxial polydomain BaTiO <sub>3</sub> thin films. <i>Journal of Materials Research</i> , <b>2007</b> , 22, 1384-1389	2.5	5
77	Nanosecond-Scale Domain Dynamics in BaTiO <sub>3</sub> Probed by Time-Resolved X-Ray Diffraction. <i>Ferroelectrics</i> , <b>2003</b> , 290, 115-124	0.6	5
76	Pressure dependence of the blue luminescence in Mg-doped GaN. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 2536-2538	3.4	5
75	Dynamic Response of the Electro-Optic Effect in Epitaxial Ferroelectric Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 597, 157		5
74	Solid phase epitaxy of Bi <sub>2</sub> Sr <sub>2</sub> CaCu <sub>2</sub> O <sub>x</sub> superconducting thin films. <i>Journal of Applied Physics</i> , <b>1993</b> , 73, 4080-4082	2.5	5
73	Preparation of Ba <sub>1-x</sub> Sr <sub>x</sub> TiO <sub>3</sub> Thin Films by Metalorganic Chemical Vapor Deposition and Their Properties. <i>Materials Research Society Symposia Proceedings</i> , <b>1993</b> , 335, 41		5
72	Symmetry properties of Er <sup>3+</sup> related centers in In <sub>1-x</sub> Ga <sub>x</sub> P with low alloy compositions. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 2461-2463	3.4	5
71	Surface photovoltage spectroscopy of surface states on indium phosphide. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 1352-1354	3.4	5

70	Charge Transport Mechanisms in a Pb <sub>2</sub> P <sub>2</sub> Se <sub>6</sub> Semiconductor. <i>ACS Photonics</i> , <b>2016</b> , 3, 1877-1887	6.3	5
69	Charge Transport in Magnetic Semiconductor p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , <b>2015</b> , 62, 2470-2474	2.9	4
68	Bilayer avalanche spin-diode logic. <i>AIP Advances</i> , <b>2015</b> , 5, 117102	1.5	4
67	Magnetoresistance in InMnAs/InAs heterojunctions and its dependence on alloy composition and temperature. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 053503	3.4	4
66	InMnAs magnetoresistive spin-diode logic <b>2012</b> ,		4
65	Optical Study of GaN Doped with Mn Grown by Metal Organic Vapor Phase Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 639, 371		4
64	Growth of MgO by Metal-Organic Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 606, 45		4
63	Deep Level Defects in Mg-Doped GaN. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 423, 525		4
62	Effect of free carriers on the luminescence efficiency of InP:Er. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 845-847	3.4	4
61	Highly Strained InAs <sub>x</sub> P <sub>1-x</sub> /InP Quantum wells Prepared by Flow Modulation Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , <b>1989</b> , 145, 145		4
60	The Chemical Vapor Deposition of Polycrystalline InP. <i>Journal of the Electrochemical Society</i> , <b>1980</b> , 127, 2747-2750	3.9	4
59	Noise sources and their limitations on the performance of compound semiconductor hard radiation detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2019</b> , 916, 133-140	1.2	4
58	Electronic defects in the halide antiperovskite semiconductor Hg <sub>3</sub> Se <sub>2</sub> I <sub>2</sub> . <i>Physical Review B</i> , <b>2017</b> , 96,	3.3	3
57	Dimensionally reduced heavy atom semiconductors as candidate materials for y-ray detection: the case of Cs <sub>2</sub> Hg <sub>6</sub> S <sub>7</sub> . <i>Materials Research Society Symposia Proceedings</i> , <b>2011</b> , 1341, 1		3
56	Alkali Metal Chalcogenides for Radiation Detection. <i>Materials Research Society Symposia Proceedings</i> , <b>2011</b> , 1341, 1		3
55	Emitter-coupled spin-transistor logic <b>2012</b> ,		3
54	Magnetocapacitance effect in InMnAs/InAs p-n heterojunctions. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2008</b> , 26, 1526		3
53	Phonon-assisted deep level luminescence in heavily Mg-doped InGaN. <i>Journal of Electronic Materials</i> , <b>2004</b> , 33, 431-435	1.9	3

52	Erbium-Doped Barium Titanate Thin Film Waveguides for Integrated Optical Amplifiers. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 688, 1		3
51	Defect Luminescence in Heavily Mg Doped GaN. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>1999</b> , 4, 968-973		3
50	Electrical Properties of Oxygen Doped GaN Grown by Metalorganic Vapor Phase Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 595, 1		3
49	Rare-Earth Doped Epitaxial InGaP and its Optical Properties. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 422, 247		3
48	Epitaxial growth of (Sr <sub>1-x</sub> Cax)CuO <sub>2</sub> thin film with the infinite-layer structure by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 1951-1953	3-4	3
47	Low Temperature Preparation of Y-Ba-Cu-O High T <sub>c</sub> Superconducting Thin Films by Plasma-Enhanced Organometallic Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , <b>1989</b> , 169, 593		3
46	Organometallic Chemical Vapor Deposition of Strontium Titanate thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1989</b> , 168, 375		3
45	Vapor phase epitaxy of InP using flow modulation. <i>Applied Physics Letters</i> , <b>1986</b> , 49, 564-566	3-4	3
44	HREM In-Situ Studies of Electron Irradiation Effects in Oxides. <i>Materials Research Society Symposia Proceedings</i> , <b>1988</b> , 100, 635		3
43	Function of cobalt and platinum on p-InP in the photoevolution of hydrogen from alkaline solutions. <i>Applied Physics Letters</i> , <b>1986</b> , 49, 829-830	3-4	3
42	Characterization of deep level defects in Tl <sub>6</sub> I <sub>4</sub> S single crystals by photo-induced current transient spectroscopy. <i>Journal Physics D: Applied Physics</i> , <b>2015</b> , 48, 075303	3	2
41	Cyclotron resonance in InMnAs and InMnSb ferromagnetic films. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 334, 012056	0.3	2
40	Interfacial Layer Effects in Ba <sub>1-x</sub> Sr <sub>x</sub> TiO <sub>3</sub> Thick Films prepared by Plasma Spray. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 758, 271		2
39	Photoluminescence Studies of p-type GaN:Mg Co-doped with Oxygen. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 639, 6391		2
38	Dielectric Properties of Spray Deposited BaTiO <sub>3</sub> and Ba <sub>0.68</sub> Sr <sub>0.32</sub> TiO <sub>3</sub> . <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 698, 361		2
37	Luminescence Efficiency of Erbium-Doped BaTiO <sub>3</sub> Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 597, 15		2
36	Excitation Properties of Er-Doped GaP from Photoluminescence and High Pressure Studies. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 422, 279		2
35	1.54 μm Electroluminescence from Erbium Doped Gallium Phosphide Diodes. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 422, 345		2

34	The Optical Properties of Channel Waveguides in BaTiO <sub>3</sub> Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 446, 349		2
33	Photoluminescent Properties of ZnO Layers Prepared by Organometallic Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , <b>1987</b> , 102, 149		2
32	Deep levels in vapor epitaxial indium phosphide grown in the presence of ammonia. <i>Journal of Applied Physics</i> , <b>1985</b> , 57, 4616-4618	2.5	2
31	Photoluminescence spectroscopy of excitonic emission in CsPbCl <sub>3</sub> perovskite single crystals. <i>Journal of Luminescence</i> , <b>2022</b> , 243, 118661	3.8	2
30	Deep Level and Near-Band-Edge Recombination in Semiconducting Antiperovskite Hg <sub>3</sub> Se <sub>2</sub> I <sub>2</sub> Single Crystals. <i>Advanced Optical Materials</i> , <b>2018</b> , 6, 1800328	8.1	2
29	Excitons in CsPbBr <sub>3</sub> Halide Perovskite. <i>Journal of Physical Chemistry Letters</i> , <b>2021</b> , 12, 9301-9307	6.4	2
28	Combinatorial Generation and Analysis of Nanometer- and Micrometer-Scale Silicon Features via Dip-Pen Nanolithography and Wet Chemical Etching <b>2000</b> , 12, 1600		2
27	Monte Carlo simulation of transport properties in wide gap Hg <sub>3</sub> Se <sub>2</sub> I <sub>2</sub> . <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 115003	1.8	1
26	Purification and Improved Nuclear Radiation Detection of Tl <sub>6</sub> Si <sub>4</sub> Semiconductor. <i>Crystal Growth and Design</i> , <b>2019</b> , 19, 4738-4744	3.5	1
25	Integrated BaTiO <sub>3</sub> modulator with 8 dB extinction at 50 GHz and 25 km reach <b>2016</b> ,		1
24	Mn doped InSb studied at the atomic scale by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 222102	3.4	1
23	High-performance computing based on spin-diode logic <b>2014</b> ,		1
22	Characterization of InMnSb epitaxial films for spintronics. <i>Journal of Physics: Conference Series</i> , <b>2012</b> , 371, 012032	0.3	1
21	The Effects Of Substrate Thermal Mismatch on the Domain Structure of MOCVD-Derived Potassium Niobate Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1997</b> , 474, 31		1
20	Epitaxial Ferroelectric Oxides for Electro-Optic and Non-Linear Optical Applications. <i>Materials Research Society Symposia Proceedings</i> , <b>1997</b> , 495, 23		1
19	Simulation and Fabrication of Two Dimensional Nonlinear Photonic Crystals using Barium Titanate Thin Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2007</b> , 1014, 1		1
18	Deep Donor-Acceptor Pair Luminescence in Codoped GaN. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 743, L5.8.1		1
17	Strain in Epitaxial BaTiO <sub>3</sub> Thin Films Prepared by MOCVD. <i>Materials Research Society Symposia Proceedings</i> , <b>1998</b> , 541, 489		1

- 16 Epitaxial KNbO<sub>3</sub> and its Nonlinear Optical Properties. *Materials Research Society Symposia Proceedings*, **1998**, 541, 741 1
- 15 Defect Structures in GaP/Si. *Materials Research Society Symposia Proceedings*, **1995**, 399, 431 1
- 14 Defects and Electronic Transport in Rare Earth Doped Epitaxial SrTiO<sub>3</sub> Thin Films. *Materials Research Society Symposia Proceedings*, **1996**, 433, 21 1
- 13 Ferroelectric Properties of a Axis Textured BaTiO<sub>3</sub> Thin Films. *Materials Research Society Symposia Proceedings*, **1993**, 310, 319 1
- 12 Heteroepitaxial Bi<sub>2</sub>Sr<sub>2</sub>CaCu<sub>2</sub>O<sub>x</sub> Superconducting thin films Deposited on LaAlO<sub>3</sub> by Solid Phase Epitaxy and OMCVD. *Materials Research Society Symposia Proceedings*, **1992**, 275, 443 1
- 11 Routes to High-T<sub>c</sub> Superconducting Tl-Ba-Ca-Cu-O Films Using Organometallic Chemical Vapor Deposition. *Materials Research Society Symposia Proceedings*, **1989**, 169, 623 1
- 10 Ultra-Wide Bandwidth, Thin Film Electro-Optic Modulators. *Ceramic Transactions*, 237-241 0.1 1
- 9 MAGNETORESISTANCE OF NARROW GAP MAGNETIC SEMICONDUCTOR HETEROJUNCTIONS. *Spin*, **2013**, 03, 1340011 1.3
- 8 Ferroelectric Thin Film Microcavities and their Optical Resonant Properties. *Materials Research Society Symposia Proceedings*, **2009**, 1182, 24
- 7 Bragg Reflector Waveguide and Electro-Optic Modulator Based on Barium Titanate Epitaxial Thin Films. *Materials Research Society Symposia Proceedings*, **2007**, 1014, 1
- 6 Deep Level Formation in Undoped and Oxygen-Doped GaN. *Materials Research Society Symposia Proceedings*, **2000**, 639, 11561
- 5 Erbium-Doped Barium Titanate Thin Film Waveguides for Integrated Optical Amplifiers. *Materials Research Society Symposia Proceedings*, **2001**, 694, 1
- 4 Defect Luminescence in Heavily Mg Doped GaN. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1
- 3 The Morphological Stability of Strained Epitaxial Layers. *Materials Research Society Symposia Proceedings*, **1996**, 440, 335
- 2 Deposition of Strontium Barium Niobate Thin Films by Metal-Organic Chemical Vapor Deposition and Their Nonlinear Optical Properties. *Materials Research Society Symposia Proceedings*, **1994**, 361, 167
- 1 Enhanced Photoluminescence from Erbium-Doped Gap Microdisk Resonator. *Materials Research Society Symposia Proceedings*, **1995**, 392, 229